

128K x 32 SRAM MODULE

PUMA 68S4000A-35/X394

Issue 4.2 : September 1997

Description

The PUMA 68S4000A/X394 is a 4Mbit CMOS High Speed Static RAM organised as 128K x 32 in a JEDEC 68 pin surface mount PLCC, with an access time of 35ns. /X394 denotes customer specific pinout. The output width is user configurable as 8 , 16 or 32 bits using four Chip Selects (CS1~4) and four Write Enables (WE1~4).

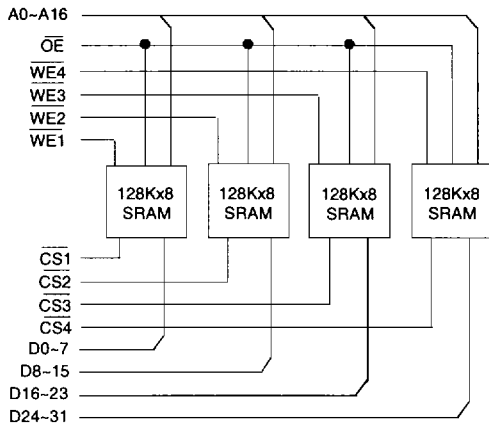
The device features low power standby, multiple ground pins for maximum noise immunity and TTL compatible inputs and outputs. The module offers a dramatic space saving advantage over four standard 128K x 8 devices. A low power standby option with 2V data retention mode is available.

Based on Alliance AS7C1024/L parts.

Features

- Very Fast Access Time of 35ns.
- JEDEC 68 pin surface mount PLCC.
- User Configurable as 8 / 16 / 32 bit wide output.
- Operating Power : 2.86 W (max)
- Standby Power : -L Part 44 mW (max)
- TTL Compatible Inputs and Outputs.
- Fully Static operation.
- Multiple ground pins for maximum noise immunity.
- Single 5V±10% Power supply.

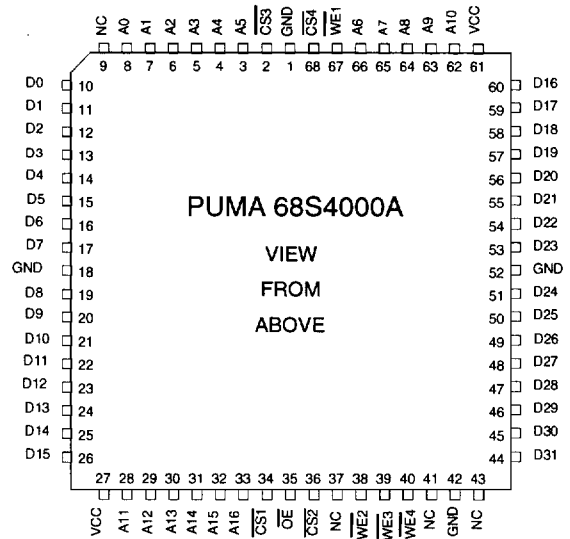
Block Diagram



Pin Functions

| | |
|-------------------|-----------------------|
| Address Inputs | A0 - A16 |
| Data Input/Output | D0 - D31 |
| Chip Select | CS1-4 |
| Write Enable | WE1~4 |
| Output Enable | OE |
| No Connect | NC |
| Power (+5V) | V_{CC} |
| Ground | GND |

Pin Definition



Package Details

Plastic 68 J-Leaded JEDEC PLCC

Refer to page 7

DC OPERATING CONDITIONS

Absolute Maximum Ratings ⁽¹⁾

| Parameter | Symbol | Min | Typ | Max | Unit |
|--|-------------------------------|------|-----|-----|------|
| Voltage on any pin relative to V _{SS} | V _T ⁽²⁾ | -0.5 | - | 7.0 | V |
| Power Dissipation | P _T | - | - | 5.0 | W |
| Storage Temperature | T _{STG} | -65 | - | 150 | °C |

Notes : (1) Stresses above those listed may cause permanent damage to the device. This is a stress rating only and functional operation of the device at those or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

(2) V_T can be -3.0V pulse of less than 10ns.

Recommended Operating Conditions

| Parameter | Symbol | Min | Typ | Max | Unit |
|-----------------------|------------------------------|------|-----|----------------------|---------------|
| Supply Voltage | V _{CC} | 4.5 | 5.0 | 5.5 | V |
| Input High Voltage | V _{IH} | 2.2 | - | V _{CC} +0.5 | V |
| Input Low Voltage | V _{IL} | -0.3 | - | 0.8 | V |
| Operating Temperature | (Commercial) T _A | 0 | - | 70 | °C |
| | (Industrial) T _{AI} | -40 | - | 85 | °C (Suffix I) |

DC Electrical Characteristics (V_{CC}=5V±10%, T_A = -40°C to +85°C)

| Parameter | Symbol | Test Condition | Min | Typ | max | Unit |
|--|------------------------------------|---|-----|-----|-----|------|
| I/P Leakage Current Address, \overline{OE} , \overline{WE} | I _{LI} | 0V ≤ V _{IN} ≤ V _{CC} | -20 | - | 20 | μA |
| Output Leakage Current | I _{LO} | $\overline{CS} = V_{IH}$, V _{I/O} = GND to V _{CC} | -20 | - | 20 | μA |
| Operating Supply Current | 32-bit mode I _{CC32} | Min. Cycle, $\overline{CS} = V_{IL}$, f=f _{MAX} , I _{OUT} = 0mA | - | - | 520 | mA |
| | 16-bit mode I _{CC16} | As Above. | - | - | 320 | mA |
| | 8-bit mode I _{CC8} | As Above. | - | - | 280 | mA |
| Standby Supply Current | TTL levels I _{SB1} | $\overline{CS} = V_{IH}$, f=f _{MAX} | - | - | 205 | mA |
| | CMOS levels I _{SB2} | $\overline{CS} \geq V_{CC}-0.2V$, 0.2 ≤ V _{IN} ≤ V _{CC} -0.2V, f=0 | - | - | 62 | mA |
| | -L Version (CMOS) I _{SB3} | $\overline{CS} \geq V_{CC}-0.2V$, 0.2 ≤ V _{IN} ≤ V _{CC} -0.2V, f=0 | - | - | 12 | mA |
| Output Voltage | V _{OL} | I _{OL} = 8.0mA | - | - | 0.4 | V |
| | V _{OH} | I _{OH} = -4.0mA | 2.4 | - | - | V |

Notes :

1/ Typical values are at V_{CC}=5.0V, T_A=25°C and specified loading.

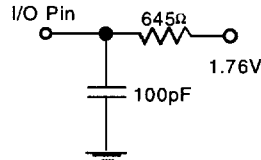
2/ At f=f_{MAX} address and data inputs are cycling at maximum frequency.

Capacitance ($V_{CC}=5V\pm 10\%$, $T_A=25^\circ C$) Note: Capacitance calculated, not measured.

| Parameter | Symbol | Test Condition | max | Unit |
|---|-----------|----------------|-----|------|
| Input Capacitance (Address, \overline{OE} , \overline{WE}) | C_{IN1} | $V_{IN} = 0V$ | 30 | pF |
| I/P Capacitance (other) | C_{IN2} | $V_{IN} = 0V$ | 7 | pF |
| I/O Capacitance | C_{IO} | $V_{IO} = 0V$ | 38 | pF |

AC Test Conditions **Output Load**

- * Input pulse levels: 0V to 3.0V
- * Input rise and fall times: 5ns
- * Input and Output timing reference levels: 1.5V
- * Output load: see diagram
- * $V_{CC}=5V\pm 10\%$



Operation Truth Table

| \overline{CS} | \overline{OE} | \overline{WE} | DATA PINS | SUPPLY CURRENT | MODE |
|-----------------|-----------------|-----------------|----------------|-------------------------------|---------|
| H | X | X | High Impedance | $I_{SB1}, I_{SB2}, I_{SB3}$ | Standby |
| L | L | H | Data Out | $I_{CC32}, I_{CC16}, I_{CC8}$ | Read |
| L | H | L | Data In | $I_{CC32}, I_{CC16}, I_{CC8}$ | Write |
| L | L | L | Data In | $I_{CC32}, I_{CC16}, I_{CC8}$ | Write |
| L | H | H | High-Impedance | $I_{SB1}, I_{SB2}, I_{SB3}$ | High-Z |

Notes : H = V_{IH} : L = V_{IL} : X = V_{IH} or V_{IL}

Low V_{CC} Data Retention Characteristics - L Version Only

| Parameter | Symbol | Test Condition | min | typ ⁽¹⁾ | max | Unit |
|--------------------------------------|---------------------|--|----------|--------------------|-----|------|
| V_{CC} for Data Retention | V_{DR} | $\overline{CS} \geq V_{CC} - 0.2V$ | 2.0 | - | - | V |
| Data Retention Current | $I_{CCDR1}^{(1,2)}$ | $V_{CC} = 3.0V, \overline{CS} \geq V_{CC} - 0.2$ | - | - | 4 | mA |
| Chip Deselect to Data Retention Time | t_{CDR} | See Retention Waveform | 0 | - | - | ns |
| Operation Recovery Time | t_R | See Retention Waveform | t_{RC} | - | - | ms |

- Notes (1) Typical figures are measured at 25°C.
 (2) This parameter is guaranteed not tested.

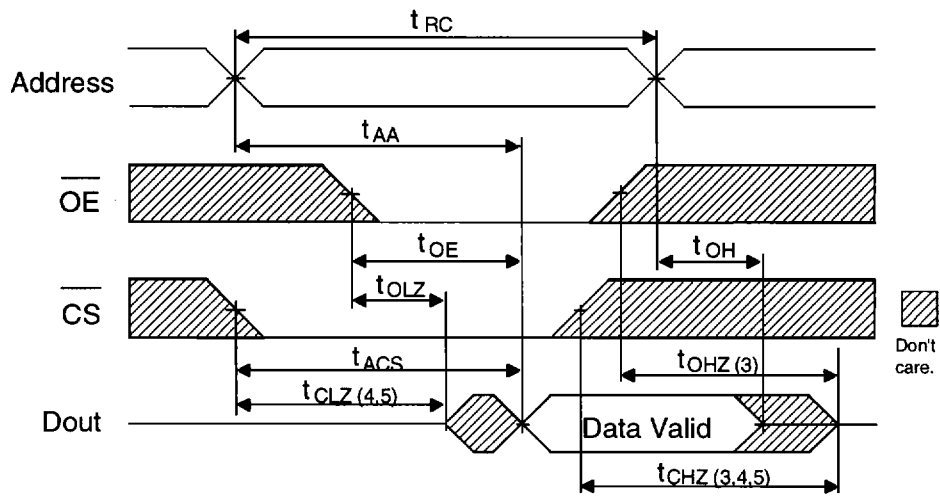
AC OPERATING CONDITIONS**Read Cycle**

| <i>Parameter</i> | <i>Symbol</i> | <i>min</i> | <i>max</i> | <i>Unit</i> |
|------------------------------------|---------------|------------|------------|-------------|
| Read Cycle Time | t_{RC} | 35 | - | ns |
| Address Access Time | t_{AA} | - | 35 | ns |
| Chip Select Access Time | t_{ACS} | - | 35 | ns |
| Output Enable to Output Valid | t_{OE} | - | 12 | ns |
| Output Hold from Address Change | t_{OH} | 3 | - | ns |
| Chip Selection to Output in Low Z | t_{CLZ} | 3 | - | ns |
| Output Enable to Output in Low Z | t_{OLZ} | 0 | - | ns |
| Chip Deselection to O/P in High Z | t_{CHZ} | 0 | 12 | ns |
| Output Disable to Output in High Z | t_{OHZ} | 0 | 12 | ns |

Write Cycle

| <i>Parameter</i> | <i>Symbol</i> | <i>min</i> | <i>max</i> | <i>Unit</i> |
|---------------------------------|---------------|------------|------------|-------------|
| Write Cycle Time | t_{WC} | 35 | - | ns |
| Chip Selection to End of Write | t_{CW} | 25 | - | ns |
| Address Valid to End of Write | t_{AW} | 25 | - | ns |
| Address Setup Time | t_{AS} | 0 | - | ns |
| Write Pulse Width | t_{WP} | 17 | - | ns |
| Write Recovery Time | t_{WR} | 0 | - | ns |
| Write to Output in High Z | t_{WHZ} | 0 | 15 | ns |
| Data to Write Time Overlap | t_{DW} | 15 | - | ns |
| Data Hold from Write Time | t_{DH} | 0 | - | ns |
| Output active from end of write | t_{OW} | 2 | - | ns |

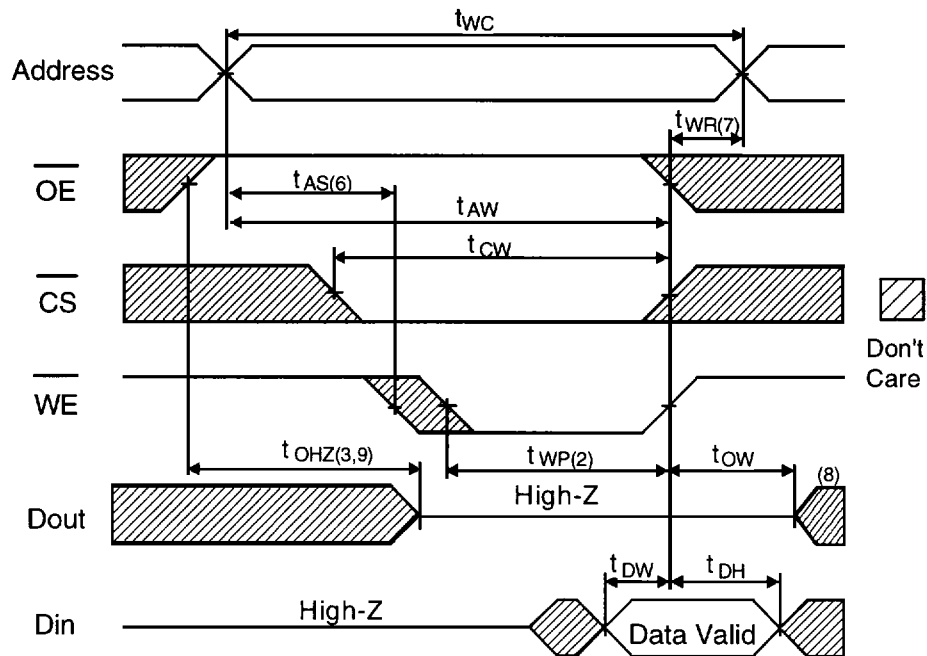
Read Cycle Timing Waveform^(1,2)



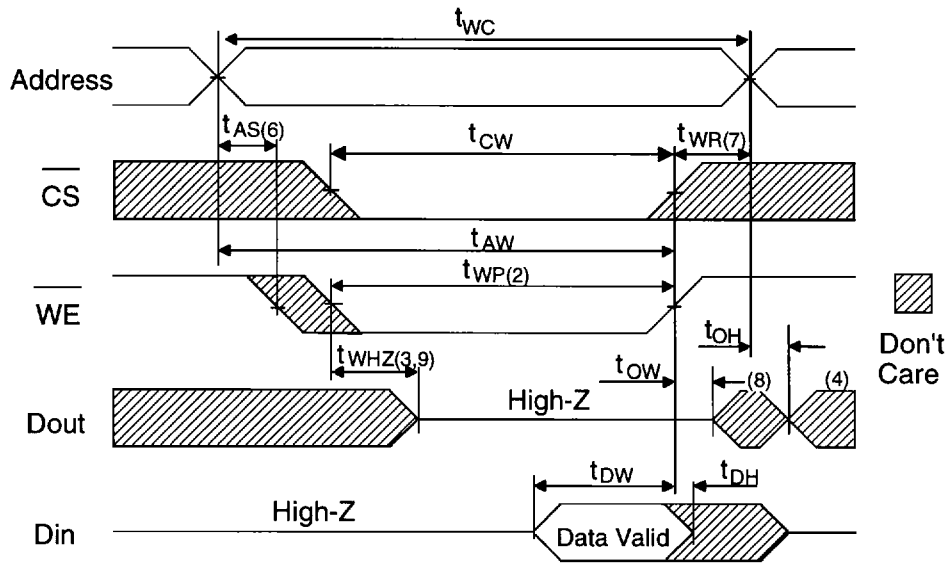
AC Read Characteristics Notes

- (1) \overline{WE} is High for Read Cycle.
- (2) All read cycle timing is referenced from the last valid address to the first transition address.
- (3) t_{CHZ} and t_{OHZ} are defined as the time at which the outputs achieve open circuit conditions and are not referenced to output voltage levels.
- (4) At any given temperature and voltage condition, t_{CHZ} (max) is less than t_{CLZ} (min) both for a given module and from module to module.
- (5) These parameters are sampled and not 100% tested.

Write Cycle No.1 Timing Waveform^(1,4)



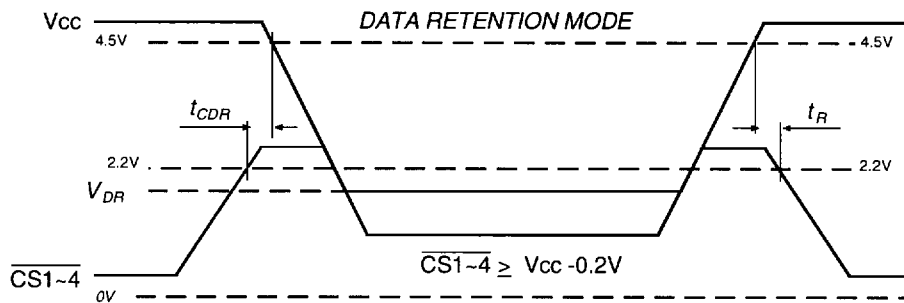
Write Cycle No.2 Timing Waveform ^(1,5)



AC Write Characteristics Notes

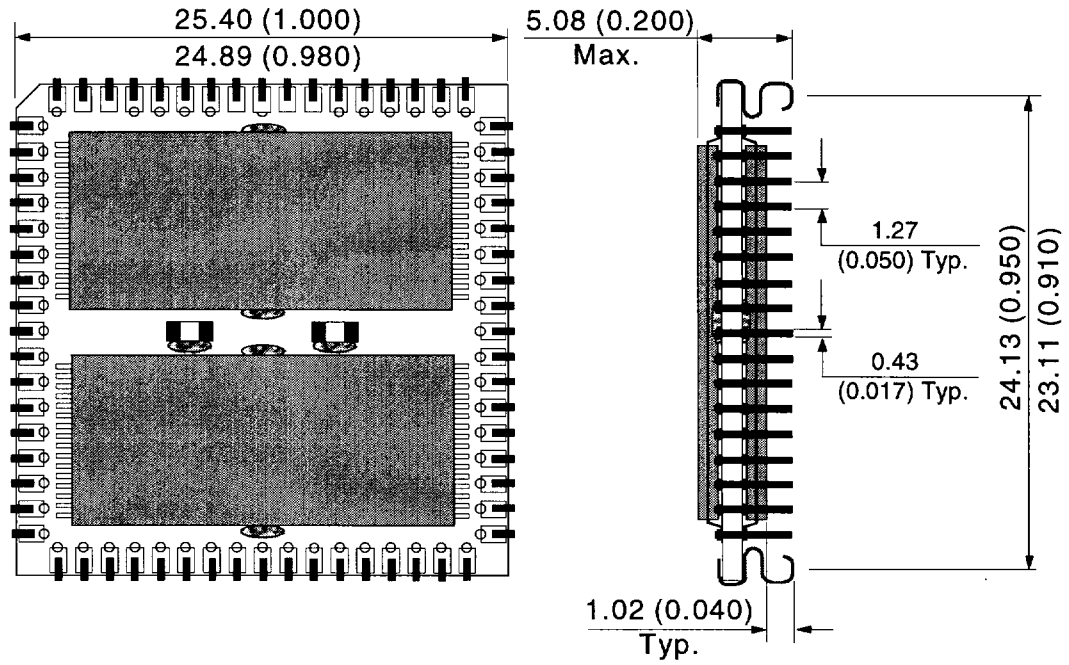
- (1) All write cycle timing is referenced from the last valid address to the first transition address.
- (2) All writes occur during the overlap of \overline{CS} and \overline{WE} low.
- (3) If \overline{OE} , \overline{CS} , and \overline{WE} are in the Read mode during this period, the I/O pins are low impedance state. Inputs of opposite phase to the output must not be applied because bus contention can occur.
- (4) \overline{Dout} is the Read data of the new address.
- (5) \overline{OE} is continuously low.
- (6) Address is valid prior to or coincident with \overline{CS} and \overline{WE} low, too avoid inadvertant writes.
- (7) \overline{CS} or \overline{WE} must be high during address transitions.
- (8) When \overline{CS} are low : I/O pins are in the output state. Input signals of opposite phase leading to the output should not be applied.
- (9) Defined as the time at which the outputs achieve open circuit conditions and are not referenced to output voltage levels. These parameters are sampled and not 100% tested.

Data Retention Waveform



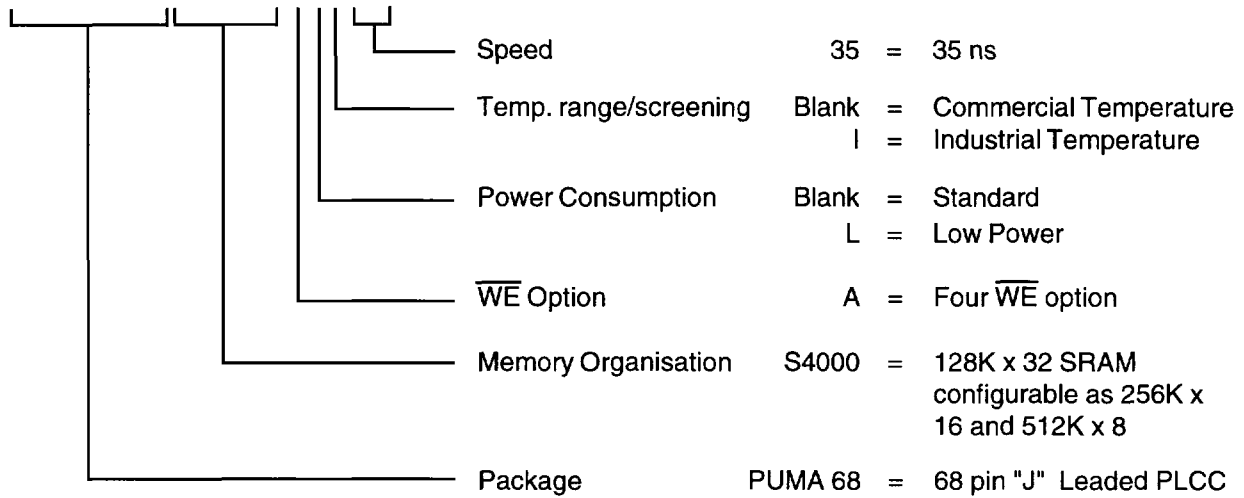
Package Information Dimensions in mm(inches)

Plastic 68 Pin JEDEC Surface mount PLCC



Ordering Information

PUMA 68S4000ALI-35/X394



Notes:

/X394 denotes customer specific pinout.